

Complementary Power Darlington

For Isolated Package Applications

Designed for general-purpose amplifiers and switching applications, where the mounting surface of the device is required to be electrically isolated from the heatsink or chassis.

- Electrically Similar to the Popular TIP122 and TIP127
- 100 V_{CEO(sus)}
- 5 A Rated Collector Current
- No Isolating Washers Required
- Reduced System Cost
- High DC Current Gain — 2000 (Min) @ I_C = 3 A_{dc}
- UL Recognized, File #E69369, to 3500 V_{RMS} Isolation

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	100	V _{dc}
Collector–Base Voltage	V _{CB}	100	V _{dc}
Emitter–Base Voltage	V _{EB}	5	V _{dc}
RMS Isolation Voltage (1) (for 1 sec, R.H. < 30%, T _A = 25°C)	Test No. 1 Per Fig. 14 Test No. 2 Per Fig. 15 Test No. 3 Per Fig. 16 V _{ISOL}	4500 3500 1500	V _{RMS}
Collector Current — Continuous Peak	I _C	5 8	A _{dc}
Base Current	I _B	0.12	A _{dc}
Total Power Dissipation* @ T _C = 25°C Derate above 25°C	P _D	30 0.24	Watt s W/° C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2 0.016	Watt s W/° C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

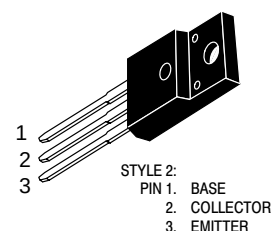
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R _{θJA}	62.5	°C/W
Thermal Resistance, Junction to Case*	R _{θJC}	4.1	°C/W
Lead Temperature for Soldering Purpose	T _L	260	°C

*Measurement made with thermocouple contacting the bottom insulated mounting surface (in a location beneath the die), the device mounted on a heatsink with thermal grease and a mounting torque of ≥ 6 in. lbs.

(1) Proper strike and creepage distance must be provided.

NPN
MJF122
PNP
MJF127

COMPLEMENTARY
SILICON
POWER DARLINGTONS
5 AMPERES
100 VOLTS
30 WATTS



CASE 221D-02
TO-220 TYPE

MJF122 MJF127

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) ($I_C = 100\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	100	—	Vdc
Collector Cutoff Current ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	10	μAdc
Collector Cutoff Current ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	10	μAdc
Emitter Cutoff Current ($V_{BE} = 5\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	2	mAdc
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 3\text{ Vdc}$) ($I_C = 3\text{ Adc}$, $V_{CE} = 3\text{ Vdc}$)	h_{FE}	1000 2000	— —	—
Collector–Emitter Saturation Voltage ($I_C = 3\text{ Adc}$, $I_B = 12\text{ mAdc}$) ($I_C = 5\text{ Adc}$, $I_B = 20\text{ mAdc}$)	$V_{CE(sat)}$	— —	2 3.5	Vdc
Base–Emitter On Voltage ($I_C = 3\text{ Adc}$, $V_{CE} = 3\text{ Vdc}$)	$V_{BE(on)}$	—	2.5	Vdc
DYNAMIC CHARACTERISTICS				
Small–Signal Current Gain ($I_C = 3\text{ Adc}$, $V_{CE} = 4\text{ Vdc}$, $f = 1\text{ MHz}$)	h_{fe}	4	—	—
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 0.1\text{ MHz}$)	MJF127 MJF122 C_{ob}	— —	300 200	pF

(1) Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

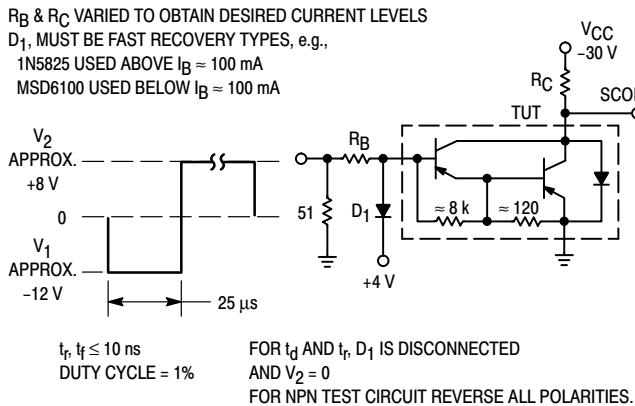


Figure 1. Switching Times Test Circuit

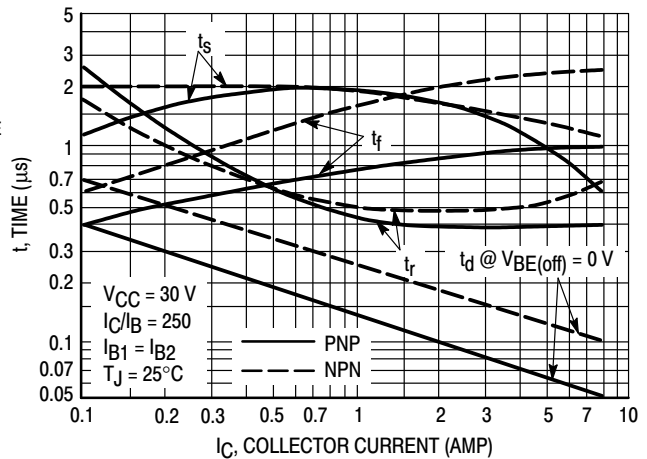


Figure 2. Typical Switching Times

MJF122 MJF127

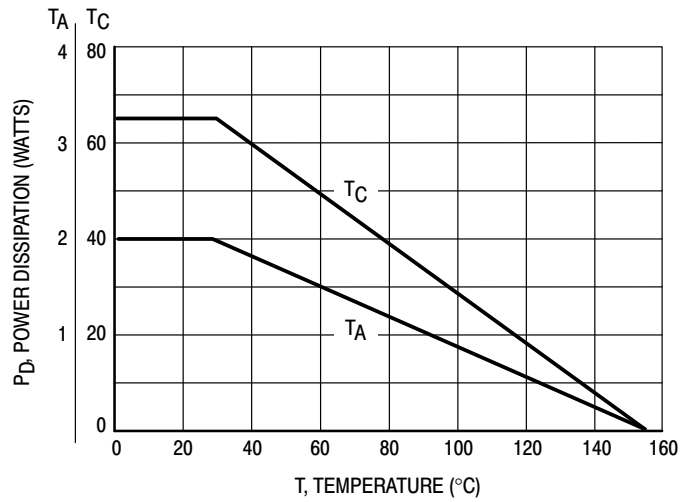


Figure 3. Maximum Power Derating

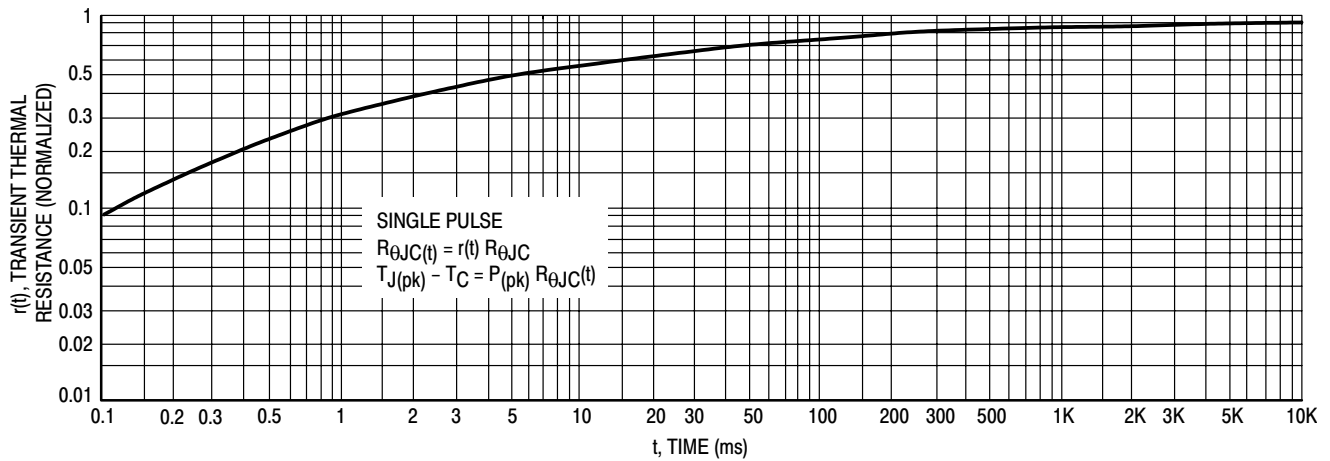


Figure 4. Thermal Response

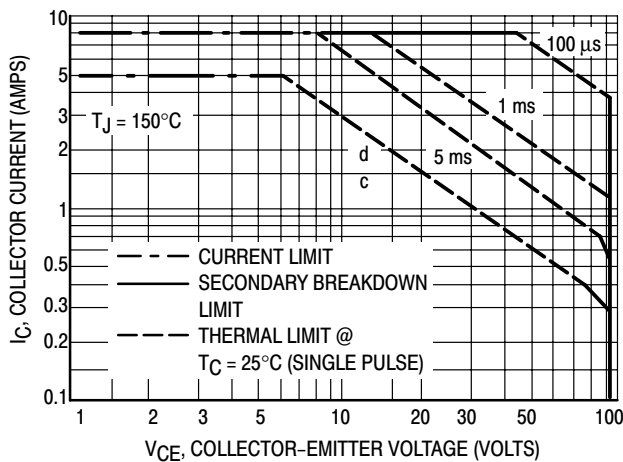


Figure 5. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Secondary breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

MJF122 MJF127

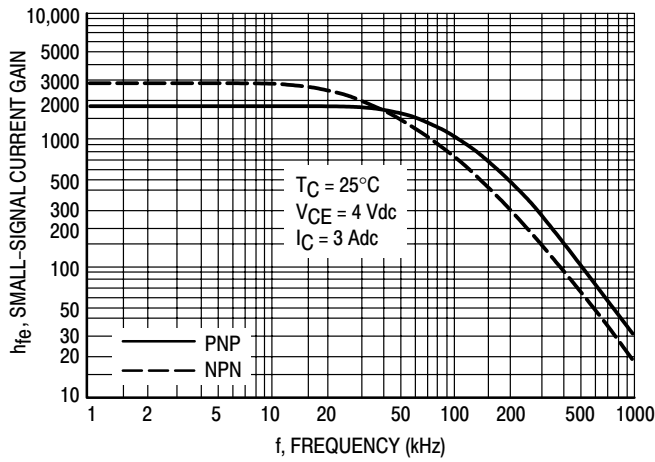


Figure 6. Typical Small-Signal Current Gain

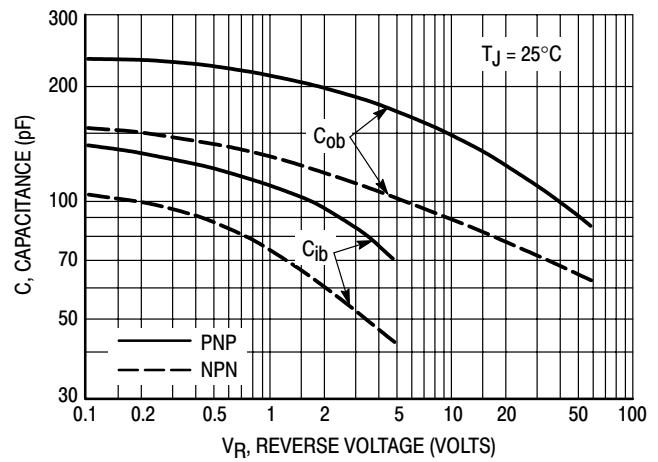


Figure 7. Typical Capacitance

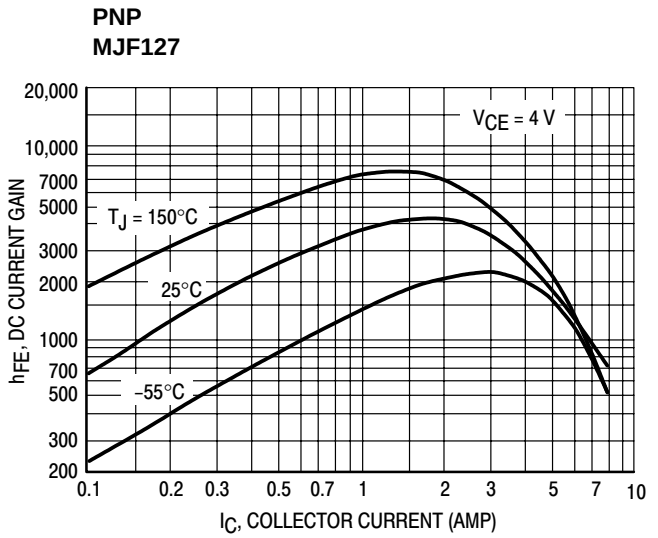
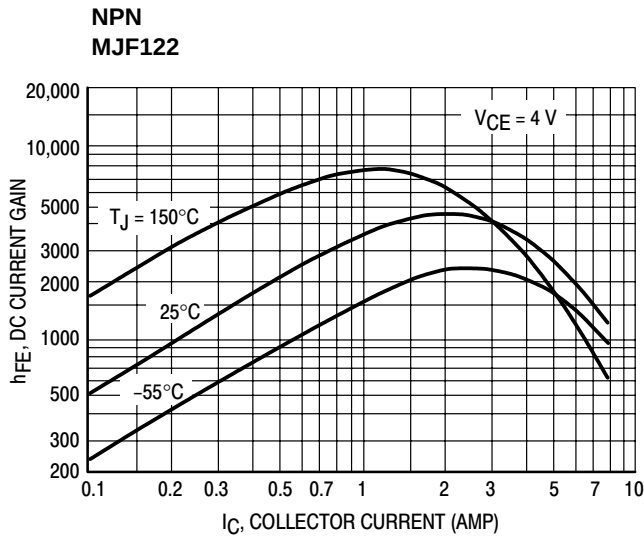


Figure 8. Typical DC Current Gain

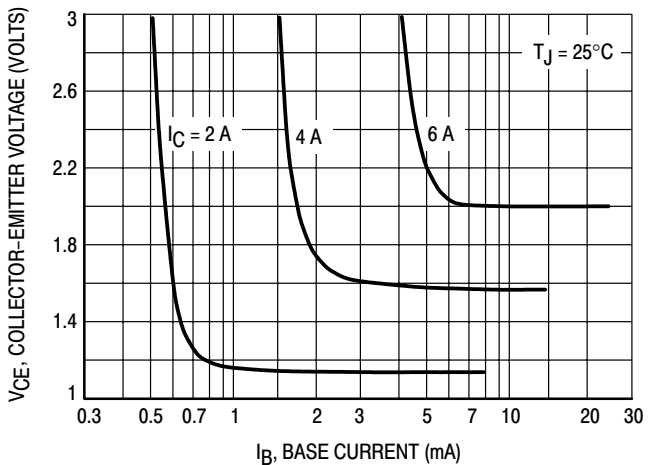
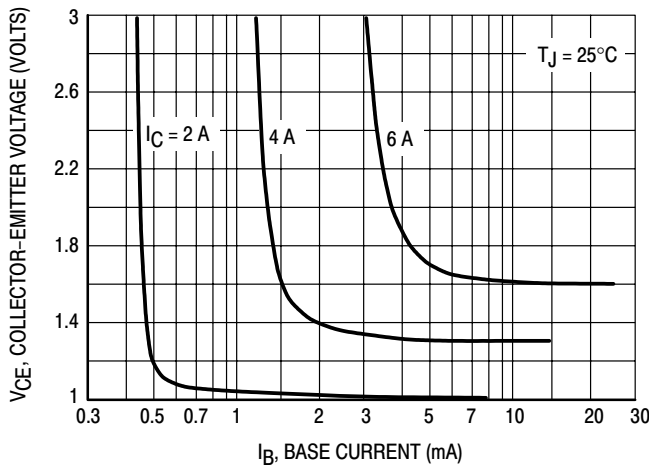
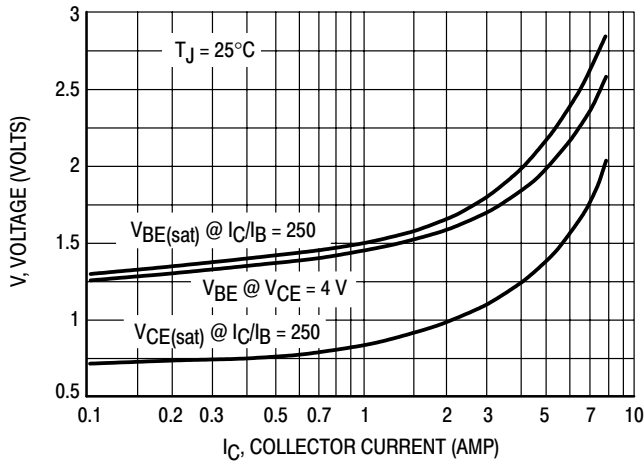


Figure 9. Typical Collector Saturation Region

MJF122 MJF127

**NPN
MJF122**



**PNP
MJF127**

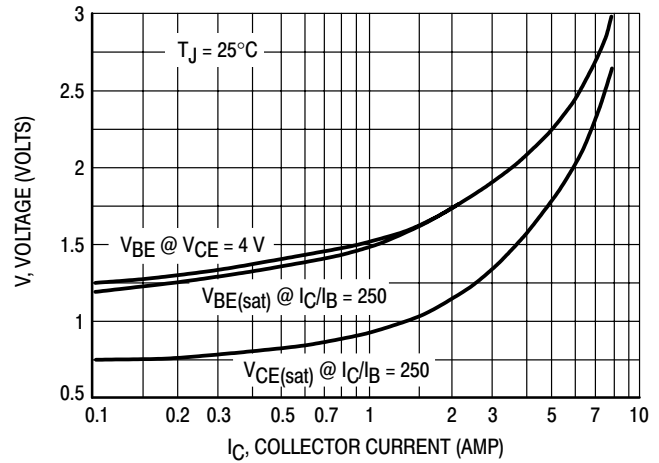


Figure 10. Typical "On" Voltages

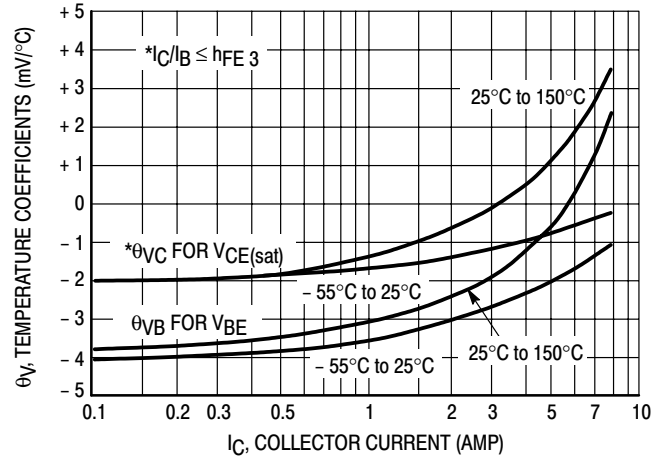
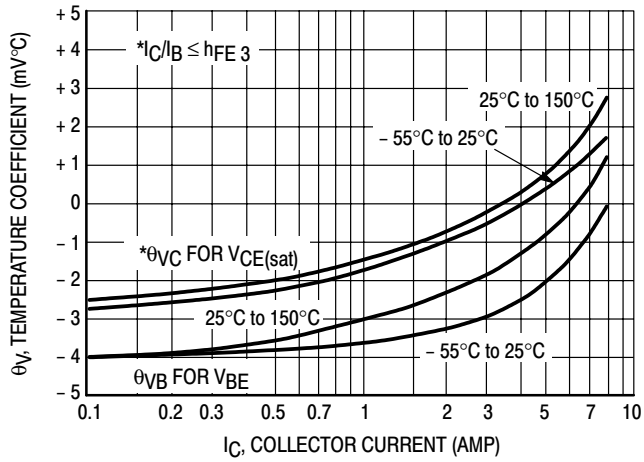


Figure 11. Typical Temperature Coefficients

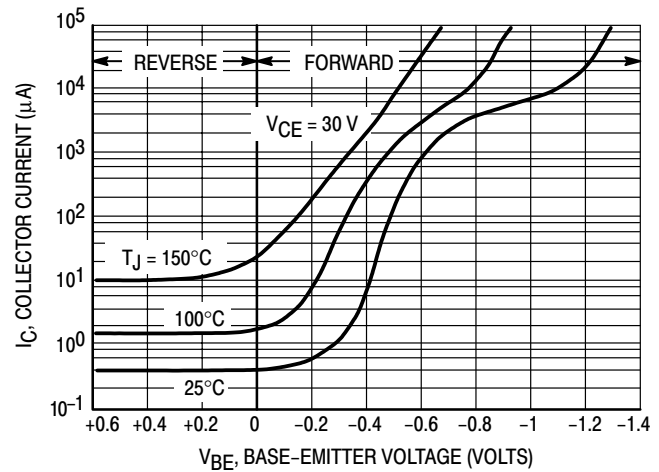
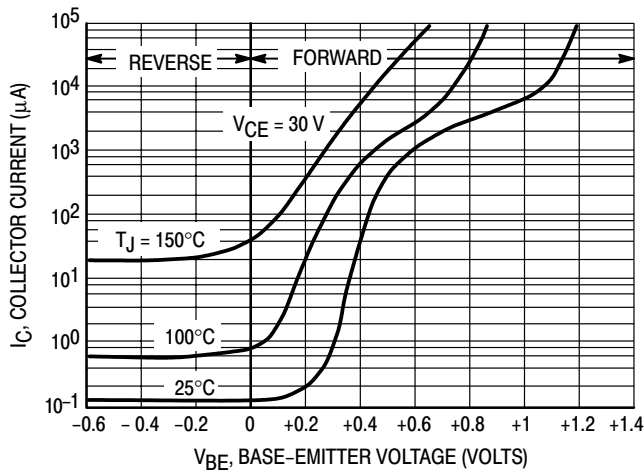
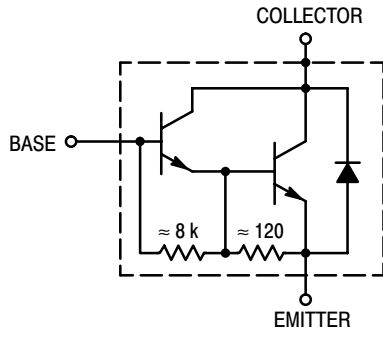


Figure 12. Typical Collector Cut-Off Region

MJF122 MJF127

NPN
MJF122



PNP
MJF127

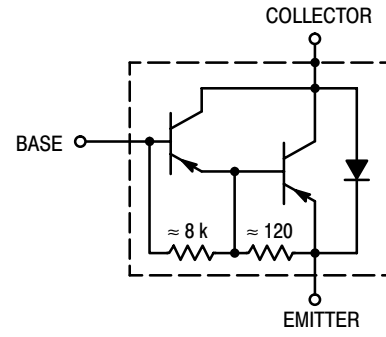


Figure 13. Darlington Schematic

TEST CONDITIONS FOR ISOLATION TESTS*

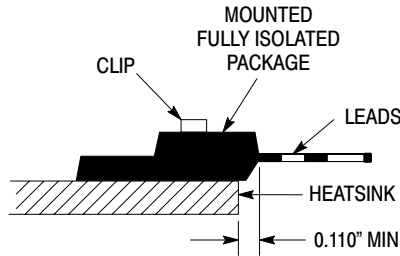


Figure 14. Clip Mounting Position for Isolation Test Number 1

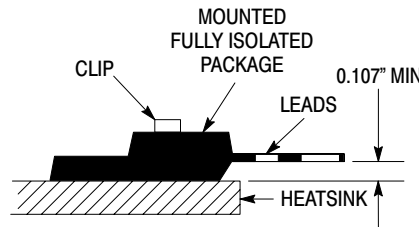


Figure 15. Clip Mounting Position for Isolation Test Number 2

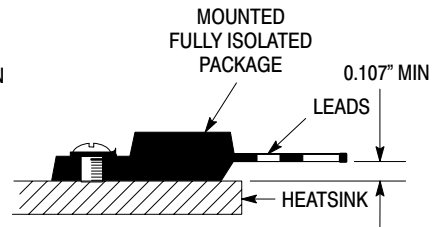


Figure 16. Screw Mounting Position for Isolation Test Number 3

*Measurement made between leads and heatsink with all leads shorted together

MOUNTING INFORMATION

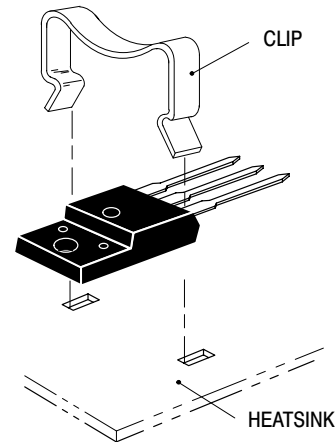
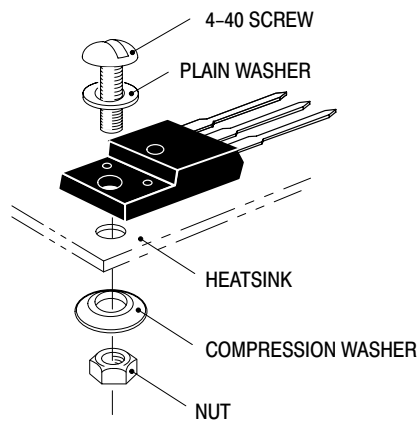


Figure 17. Typical Mounting Techniques*

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4-40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

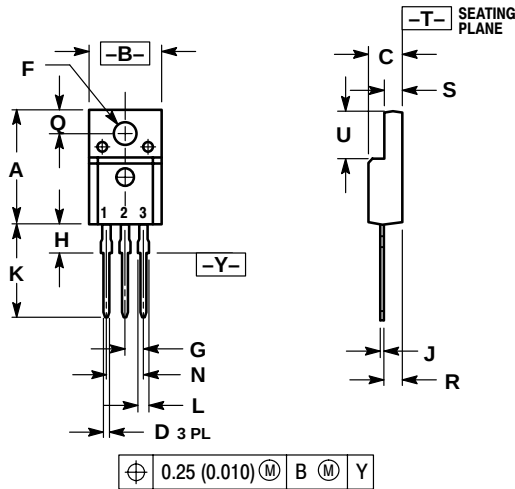
Additional tests on slotted 4-40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, ON Semiconductor does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

** For more information about mounting power semiconductors see Application Note AN1040.

MJF122 MJF127

PACKAGE DIMENSIONS

CASE 221D-02 TO-220 TYPE ISSUE D



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.621	0.629	15.78	15.97
B	0.394	0.402	10.01	10.21
C	0.181	0.189	4.60	4.80
D	0.026	0.034	0.67	0.86
F	0.121	0.129	3.08	3.27
G	0.100 BSC		2.54 BSC	
H	0.123	0.129	3.13	3.27
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
N	0.200 BSC		5.08 BSC	
Q	0.126	0.134	3.21	3.40
R	0.107	0.111	2.72	2.81
S	0.096	0.104	2.44	2.64
U	0.259	0.267	6.58	6.78

STYLE 2:

1. BASE
2. COLLECTOR
3. EMITTER

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